Hydrogen interaction with point defects in the Si-SiO2 structures and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 https://www.scientific.net/SSP.131-133.345

Interaction between point defects, extended defects and impurities in the Si-SiO2 system during the process of its formation
Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Thin solid films 2004 / 1/2, p. 53-57 : ill
https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459

Interaction between point defects, extended defects and impurities in the Si-SiO2 system during the process of its formation
Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit** Materials science and engineering : B 2004 / p. 295-298 : ill https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459

Kas III kvartali majanduskasv valmistas teile pettumuse? : [Äripäeva küsitlusele vastavad Uno Abru, Priit Kivi, Jaak Leimann ja Veikko Maripuu]
Leimann, Jaak; Abru, Uno; Kivi, Priit; Maripuu, Veikko Äripäev 1999 / 7. dets., lk. 31: portr

Point defects interaction with extended defects in the Si-SiO2 system [Electronic resource]
Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Proceedings IVC-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM]
https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties